CS-99-107

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November 17, 1999

To: Commissioner of Patents and Trademarks

Washington, D.C. 20231

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TECHNOLOGY CENTER 2800

Subject:

Serial No.

Lap Chan, K.W. J. Chew, C.L. Cha, C.T. Chua

A METHOD TO FABRICATE HORIZONTAL AIR COLUMNS UNDERNEATH METAL

INDUCTOR

Grp. Art Unit: 2811

## INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

U.S. Patent 5,828,121 to Lur et al., "Multi-Level Conduction Structure for VLSI Circuits", discloses air gaps between metal lines at different levels by etching the dielectric layers between the metal line levels.

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The following two U.S. Patents describe air gaps under inductors:

- 1) U.S. Patent 5,539,241 to Abidi et al., "Monolithic Passive Component".
- 2) U.S. Patent 5,844,299 to Merrill et al., "Integrated Inductor".
- U.S. Patent 5,880,026 to Xing et al., "Method for Air Gap Formation by Plasma Treatment of Aluminum Interconnects", discloses a process to form air gaps between conductors.
- U.S. Patent 5,880,018 to Boeck et al., "Method for Manufacturing a Low Dielectric Constant Inter-Level Integrated Circuit Structure", discloses an air gap process between lines.

Sincerely

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